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LHV870 44V Single High Performance, High Voltage Operational Amplifier

Check for Samples: LHV870

FEATURES

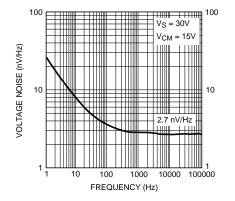
- Easily Drives 600Ω Loads
- **Output Short Circuit Protection**
- PSRR and CMRR Exceed 120dB (Typ)

APPLICATIONS

- Low Noise Industrial Applications Including Test, Measurement, and Ultrasound
- **High Quality Audio Amplification**
- High Fidelity Preamplifiers, Phono Preamps, and Multimedia
- **High Performance Professional Audio**
- **High Fidelity Equalization and Crossover Networks with Active Filters**
- **High Performance Line Drivers and Receivers**

KEY SPECIFICATIONS

- Power Supply Voltage Range ±2.5V to ±22 V
- Input Noise Density 2.7nV/√Hz (Typ)
- Slew Rate ±20V/µs (Typ)
- Gain Bandwidth Product 55 MHz (Typ)
- Open Loop Gain ($R_L = 600\Omega$) 140 dB (Typ)
- Input Bias Current 10nA (Typ)
- Input Offset Voltage 0.1mV (Typ)
- DC Gain Linearity Error 0.000009%
- THD+N ($A_V = 1$, $V_{OUT} = 3V_{RMS}$, $f_{IN} = 1$ kHz)
 - $-R_L = 2k\Omega 0.00003\%$ (Typ)
 - $-R_L = 600\Omega \ 0.00003\% \ (Typ)$



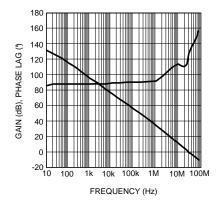
DESCRIPTION

The LHV870 is an ultra-low distortion, low noise, high slew rate operational amplifier optimized and fully specified for high performance, high voltage applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LHV870 operational amplifier delivers amplification superior signal for outstanding performance. The LHV870 combines extremely low voltage noise density (2.7nV/√Hz) with vanishingly low DC Gain Linearity Error (0.000009%) to easily satisfy the most demanding applications. To ensure that the most challenging loads are driven without compromise, the LHV870 has a high slew rate of ±20V/µs and an output current capability of ±26mA. Further, dynamic range is maximized by an output stage that drives $2k\Omega$ loads to within 1V of either power supply voltage and to within 1.4V when driving 600Ω loads.

The LHV870's outstanding CMRR (120dB), PSRR (120dB), and V_{OS} (0.1mV) give the amplifier excellent DC performance.

The LHV870 operates over a wide supply range of ±2.5V to ±22V and is unity gain stable. This operational amplifier achieves outstanding performance while driving complex loads with values as high as 100pF.

The LHV870 is available in 10-lead WQFN package.



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STRUMENTS

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Connection Diagram

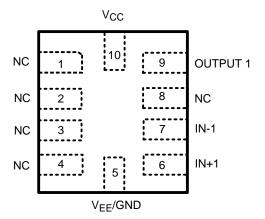


Figure 1. See Package Number - NKY0010A



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ABSOLUTE MAXIMUM RATINGS (1)(2)(3)

ADOOLOTE MAXIMOM NATH	100	
Power Supply Voltage (V _S = V ⁺ - V ⁻)	46V	
Storage Temperature	−65°C to 150°C	
Input Voltage	(V-) - 0.7V to (V+) + 0.7V	
Output Short Circuit ⁽⁴⁾	Continuous	
Power Dissipation	Internally Limited	
ESD Rating ⁽⁵⁾	2000V	
ESD Rating ⁽⁶⁾	Pins 1, 4, 7 and 8	200V
	Pins 2, 3, 5 and 6	100V
Junction Temperature		150°C
Thermal Resistance	168°C/W	

- (1) "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified.
- (2) The Electrical Characteristics tables list ensured specifications under the listed Recommended Operating Conditions except as otherwise modified or specified by the Electrical Characteristics Conditions and/or Notes. Typical specifications are estimations only and are not ensured.
- (3) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/Distributors for availability and specifications.
- (4) The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX}, θ_{JA}, and the ambient temperature, T_A. The maximum allowable power dissipation is P_{DMAX} = (T_{JMAX} T_A) / θ_{JA} or the number given in Absolute Maximum Ratings, whichever is lower.
- (5) Human body model, applicable std. JESD22-A114C.
- (6) Machine model, applicable std. JESD22-A115-A.



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OPERATING RATINGS

Temperature Range $(T_{MIN} \le T_A \le T_{MAX})$	-40°C ≤ T _A ≤ 85°C
Supply Voltage Range	±2.5V ≤ V _S ≤ ±22V

ELECTRICAL CHARACTERISTICS FOR THE LHV870⁽¹⁾

The following specifications apply for $V_S = \pm 18V$ and $\pm 22V$, $R_L = 2k\Omega$, $R_{SOURCE} = 10\Omega$, $f_{IN} = 1kHz$, $T_A = 25^{\circ}C$, unless otherwise specified.

Comple ed	Danamatan	O a statistica a	LHV	Units	
Symbol	Parameter	Conditions	Typical ⁽²⁾	Limit ⁽³⁾	(Limits)
THD+N	Total Harmonic Distortion + Noise	$A_V = 1$, $V_{OUT} = 3V_{RMS}$, $R_L = 2k\Omega$	0.00003		%
IMD	Intermodulation Distortion	$A_V = 1$, $V_{OUT} = 3V_{RMS}$ Two-tone, 60Hz & 7kHz 4:1	0.00005		%
GBWP	Gain Bandwidth Product		55	45	MHz (min)
SR	Slew Rate		±20		V/µs
FPBW	Full Power Bandwidth	V _{OUT} = 1V _{P.P} , -3dB referenced to output magnitude at f = 1kHz	10		MHz
t _s	Settling time	A _V = -1, 10V step, C _L = 100pF 0.1% error range	1.2		μs
	Equivalent Input Noise Voltage	f _{BW} = 20Hz to 20kHz	0.34	0.65	μV _{RMS} (max)
e _n	Equivalent Input Noise Density	f = 1kHz	2.5	4.7	nV / √Hz (max)
in	Current Noise Density	f = 1kHz	1.6		pA / √Hz
Vos	Officet Voltage	V _S = ±18V	±0.12		mV
	Offset Voltage	$V_S = \pm 22V$	±0.14	±2	mV (max)
$\Delta V_{OS}/\Delta Temp$	Average Input Offset Voltage Drift vs Temperature	-40°C ≤ T _A ≤ 85°C	0.1		μV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	$V_S = \pm 18V$, $\Delta V_S = 24V^{(4)}$ $V_S = \pm 22V$, $\Delta V_S = 30V$	120 120	110	dB (min)
I _B	Input Bias Current	V _{CM} = 0V	10	300	nA (max)
ΔI _{OS} /ΔTemp	Input Bias Current Drift vs Temperature	-40°C ≤ T _A ≤ 85°C	0.2		nA/°C
Ios	Input Offset Current	V _{CM} = 0V	11	100	nA (max)
V _{IN-CM} Com	Common Mada lanut Valtana Danna	V _S = ±18V	+17.1 -16.9		V
	Common-Mode Input Voltage Range	V _S = ±22V	+21.0 -20.8	(V+) - 2.0 (V-) + 2.0	V (min) V (min)
CMRR	Common Mode Dejection	V _S = ±18V -12V≤V _{CM} ≤12V	120		dB
	Common-Mode Rejection	V _S = ±22V -15V≤V _{CM} ≤15V	120	110	dB (min)
7	Differential Input Impedance		30		kΩ
Z_{IN}	Common Mode Input Impedance	-10V <v<sub>CM<10V</v<sub>	1000		МΩ

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^{(1) &}quot;Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified.

⁽²⁾ Typical values represent most likely parametric norms at T_A = +25°C, and at the Recommended Operation Conditions at the time of product characterization and are not ensured.

⁽³⁾ Datasheet min/max specification limits are specified by test or statistical analysis.

⁽⁴⁾ PSRR is measured as follows: For V_S, V_{OS} is measured at two supply voltages, ±7V and ±22V, PSRR = |20log(ΔV_{OS} / ΔV_S)|.



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ELECTRICAL CHARACTERISTICS FOR THE LHV870⁽¹⁾ (continued)

The following specifications apply for $V_S = \pm 18V$ and $\pm 22V$, $R_L = 2k\Omega$, $R_{SOURCE} = 10\Omega$, $f_{IN} = 1kHz$, $T_A = 25^{\circ}C$, unless otherwise specified.

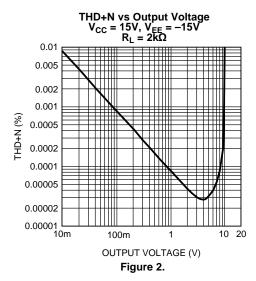
		9 11.1	LHV	LHV870		
Symbol	Parameter	Conditions	Typical ⁽²⁾	Limit ⁽³⁾	(Limits)	
A _{VOL} Open	Onen Leen Veltage Coin	$V_S = \pm 18V$ $-12V \le V_{OUT} \le 12V$ $R_L = 2k\Omega$	140		dB	
	Open Loop Voltage Gain	$V_{S} = \pm 22V$ $-15V \le V_{OUT} \le 15V$ $R_{L} = 2k\Omega$	140		dB	
V _{OUTMAX} Maximu	Maximum Output Valtage Suing	$R_L = 600\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	±16.7 ±20.4	±19.0	V V (min)	
	Maximum Output Voltage Swing	$R_L = 2k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	±17.0 ±21.0		V	
l _{out}	Output Current	$R_L = 600\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	±31 ±37	±30	mA mA (min)	
I _{OUT-CC}	Instantaneous Short Circuit Current		+53 -42		mA	
R _{OUT}	Output Impedance	f _{IN} = 10kHz Closed-Loop Open-Loop	0.01 13		ΩΩ	
Is	Total Quiescent Current	I _{OUT} = 0mA	5	6.5	mA (max)	

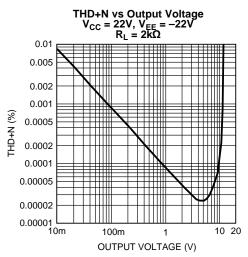
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INSTRUMENTS

TYPICAL PERFORMANCE CHARACTERISTICS





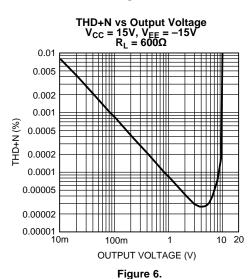
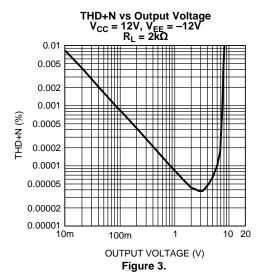
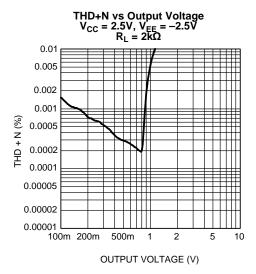


Figure 4.







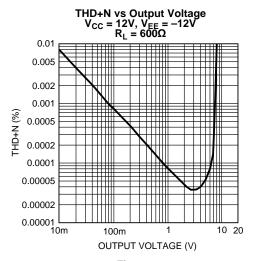


Figure 7.

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TEXAS INSTRUMENTS

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

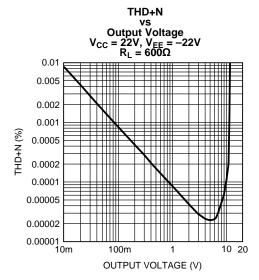
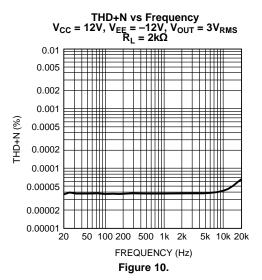
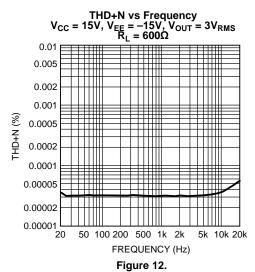
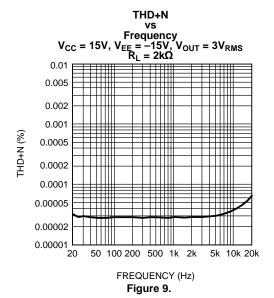
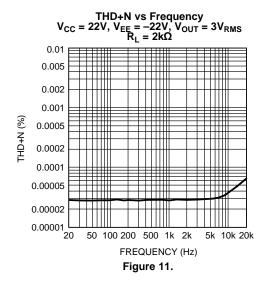


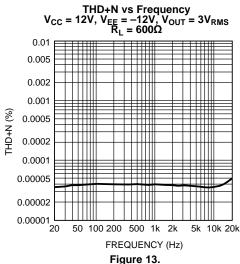
Figure 8.







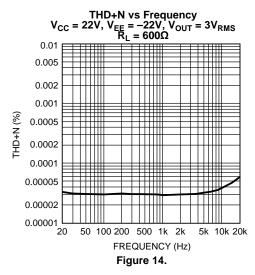




Figure

Instruments

TYPICAL PERFORMANCE CHARACTERISTICS (continued)



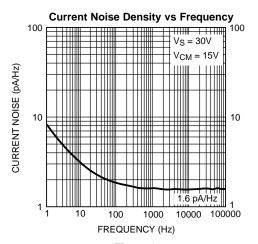


Figure 16.

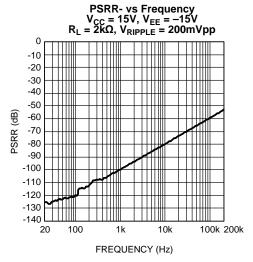
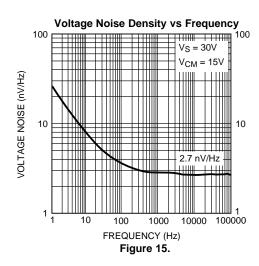
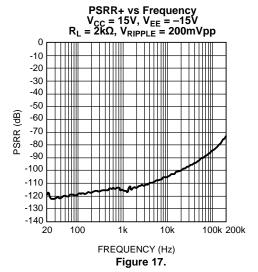


Figure 18.





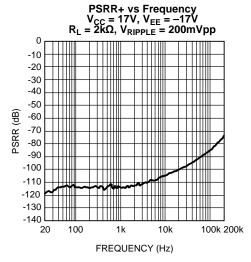


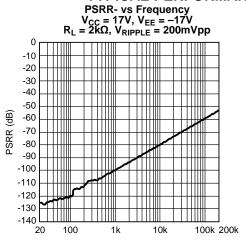
Figure 19.

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TYPICAL PERFORMANCE CHARACTERISTICS (continued)



FREQUENCY (Hz)
Figure 20.

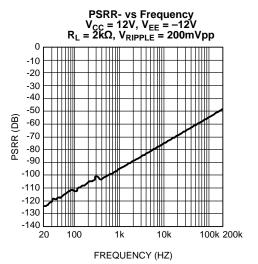


Figure 22.

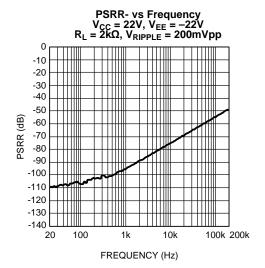


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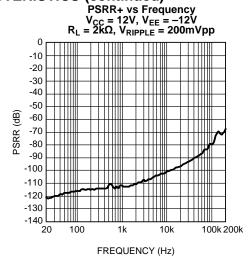


Figure 21.

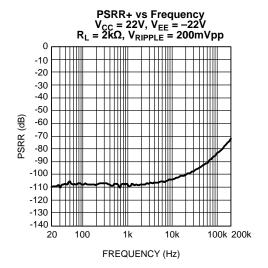


Figure 23.

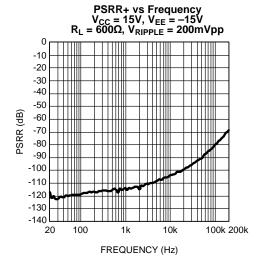


Figure 25.

INSTRUMENTS

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

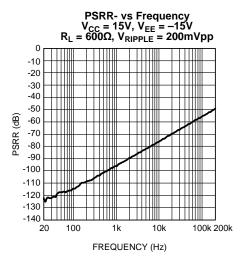


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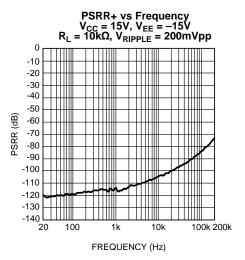


Figure 28.

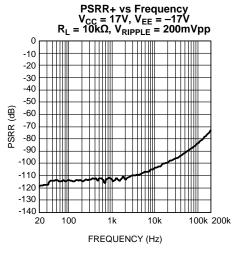


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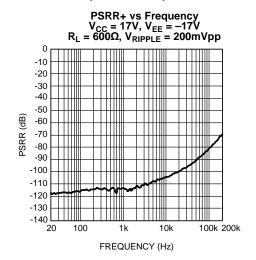


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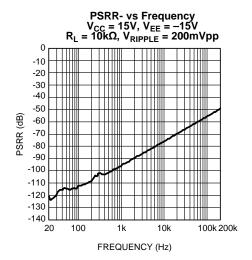


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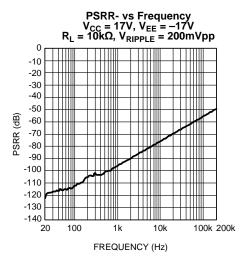


Figure 31.

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TEXAS



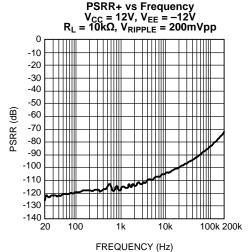


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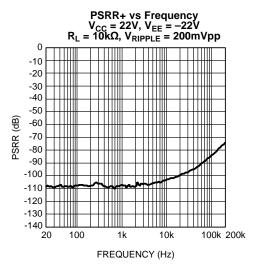


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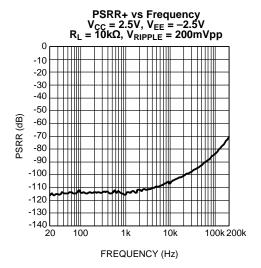


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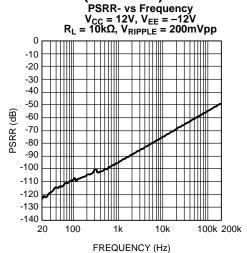


Figure 33.

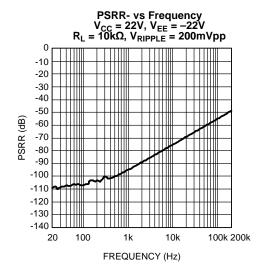


Figure 35.

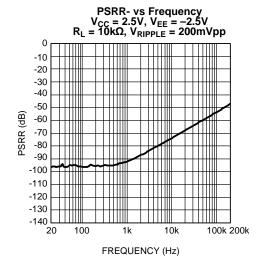


Figure 37.

Instruments

100k 200k

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

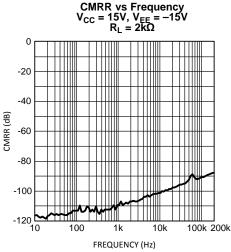


Figure 38.

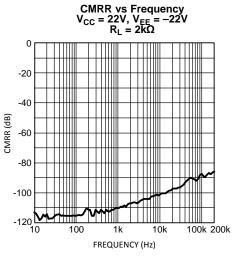
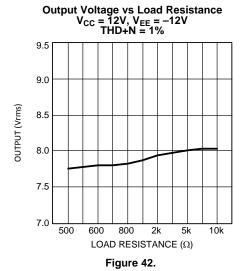


Figure 40.



CMRR vs Frequency $V_{CC} = 12V$, $V_{EE} = -12V$ $R_L = 2k\Omega$

-100

-120 L

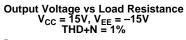
10

100

FREQUENCY (Hz) Figure 39.

10k

1k



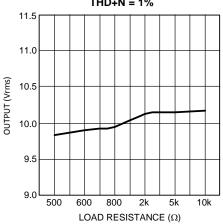


Figure 41.

Output Voltage vs Load Resistance V_{CC} = 22V, V_{EE} = -22V THD+N = 1%

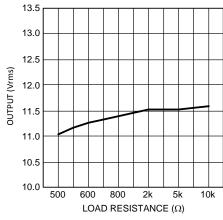


Figure 43.

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TYPICAL PERFORMANCE CHARACTERISTICS (continued)

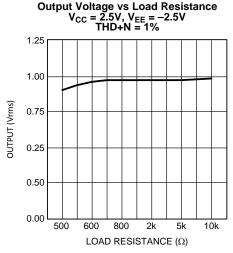


Figure 44.

Output Voltage vs Total Power Supply Voltage $R_L = 600\Omega, THD+N = 1\%$

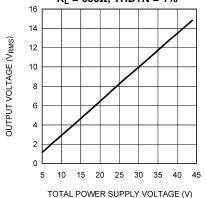
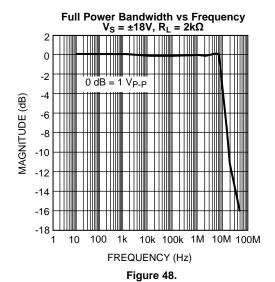


Figure 46.



Output Voltage vs Total Power Supply Voltage $R_L = 2k\Omega$, THD+N = 1%

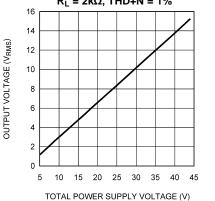
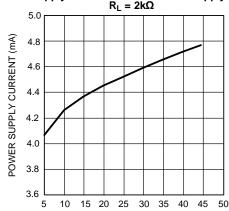
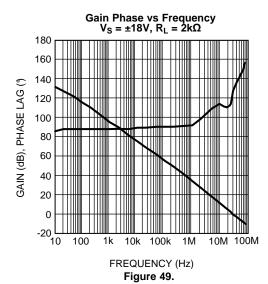


Figure 45.

Power Supply Current vs Total Power Supply Voltage $R_L=2k\Omega$



TOTAL POWER SUPPLY VOLTAGE (V) Figure 47.



Instruments

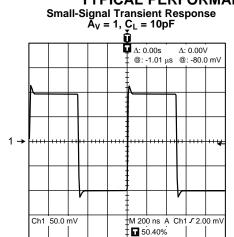


Figure 50.

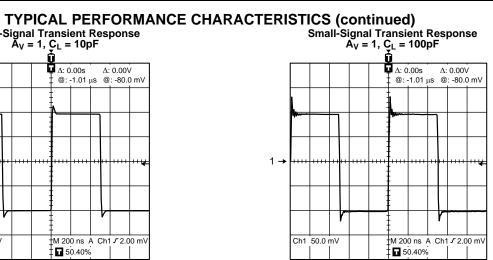


Figure 51.

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APPLICATION INFORMATION

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LHV870 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LHV870's low residual distortion is an input referred internal error. As shown in Figure 52, adding the 10Ω resistor connected between the amplifier's inverting and non-inverting inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 52.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

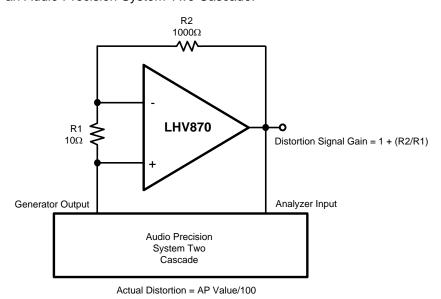
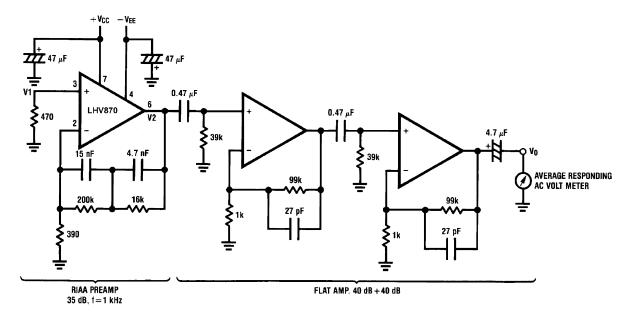


Figure 52. THD+N and IMD Distortion Test Circuit

The LHV870 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.



Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.

Total Gain: 115 dB @f = 1 kHz

Input Referred Noise Voltage: e_n = V0/560,000 (V)

Figure 53. Noise Measurement Circuit

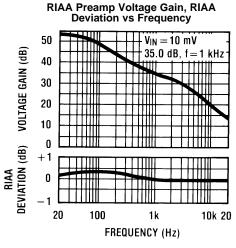


Figure 54.

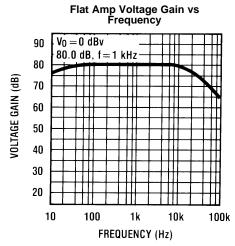
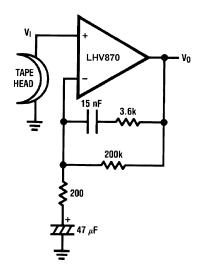


Figure 55.

Instruments

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TYPICAL APPLICATIONS



 $A_{V} = 34.5$ F = 1 kHz $E_n = 0.38 \; \mu V$ A Weighted

Figure 56. NAB Preamp

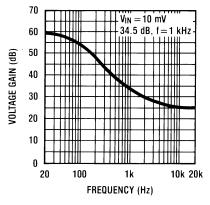
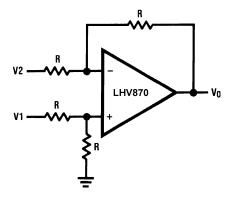


Figure 57. NAB Preamp Voltage Gain vs Frequency

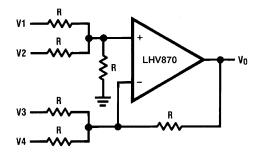


 $V_O = V1-V2$

Figure 58. Balanced to Single Ended Converter

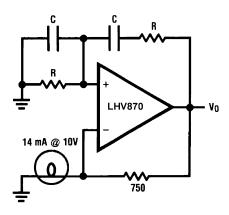
ISTRUMENTS

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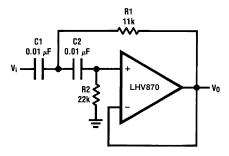
 $V_0 = V1 + V2 - V3 - V4$

Figure 59. Adder/Subtracter



$$f_0 = \frac{1}{2\pi RC}$$

Figure 60. Sine Wave Oscillator

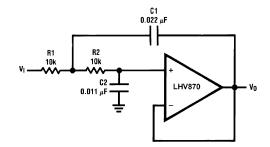


if C1 = C2 = C
$$R1 = \frac{\sqrt{2}}{2\omega_0C}$$

$$R2 = 2 \cdot R1$$
 Illustration is $f_0 = 1 \text{ kHz}$

Figure 61. Second Order High Pass Filter (Butterworth)





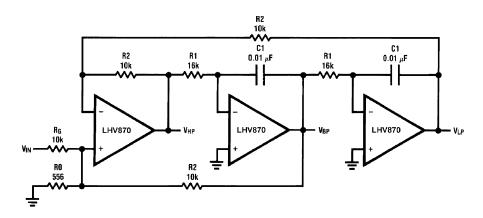
if R1 = R2 = R

$$C1 = \frac{\sqrt{2}}{\omega_0 F}$$

$$C2 = \frac{C1}{2}$$

Illustration is $f_0 = 1 \text{ kHz}$

Figure 62. Second Order Low Pass Filter (Butterworth)



$$f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$$

Illustration is $f_0 = 1 \text{ kHz}$, Q = 10, $A_{BP} = 1$

Figure 63. State Variable Filter

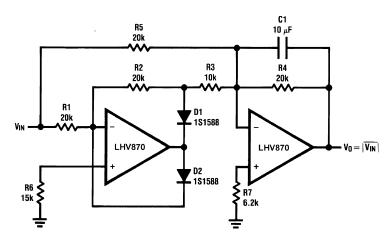


Figure 64. AC/DC Converter



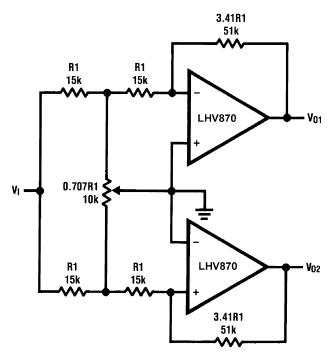


Figure 65. 2 Channel Panning Circuit (Pan Pot)

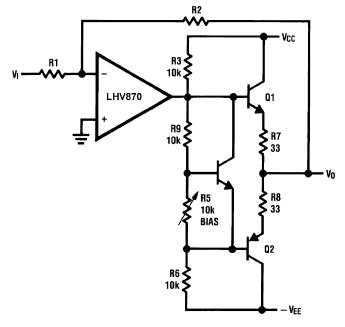
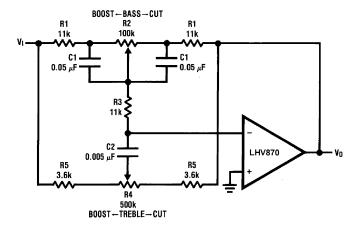


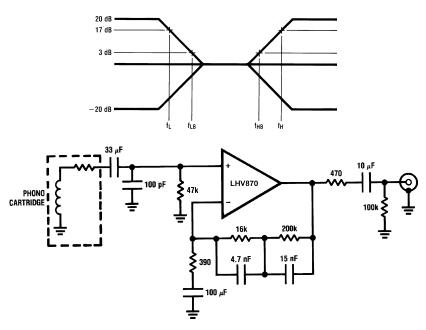
Figure 66. Line Driver





$$\begin{split} f_L &= \frac{1}{2\pi R2C1}, f_{LB} = \frac{1}{2\pi R1C1} \\ f_H &= \frac{1}{2\pi R5C2}, f_{HB} = \frac{1}{2\pi (R1 + R5 + 2R3)C2} \\ Illustration is: \\ f_L &= 32 \ Hz, \ f_{LB} = 320 \ Hz \\ f_H &= 11 \ kHz, f_{HB} = 1.1 \ kHz \end{split}$$

Figure 67. Tone Control

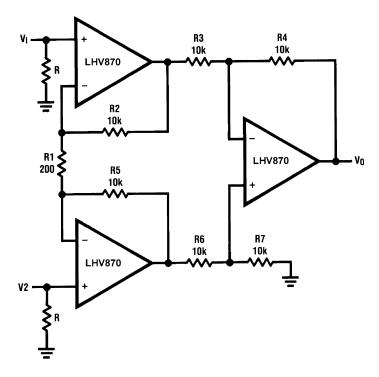


 $\begin{array}{l} A_v = 35 \text{ dB} \\ E_n = 0.33 \ \mu\text{V} \\ \text{S/N} = 90 \text{ dB} \\ \text{f} = 1 \text{ kHz} \\ \text{A Weighted}, \ \text{V}_{\text{IN}} = 10 \text{ mV} \\ \text{@f} = 1 \text{ kHz} \end{array}$

Figure 68. RIAA Preamp

INSTRUMENTS





If R2 = R5, R3 = R6, R4 = R7
$$V0 = \left(1 + \frac{2R2}{R1}\right) \frac{R4}{R3} (V2 - V1)$$
 Illustration is:
$$V0 = 101 (V2 - V1)$$

Figure 69. Balanced Input Mic Amp

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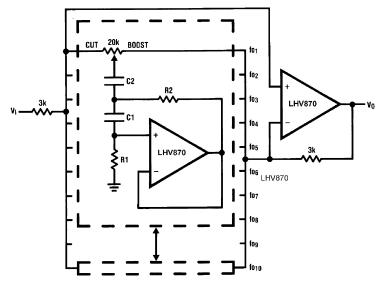


Figure 70. 10 Band Graphic Equalizer

fo (Hz)	C ₁	C ₂	R ₁	R ₂
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.82µF	68kΩ	470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

INSTRUMENTS

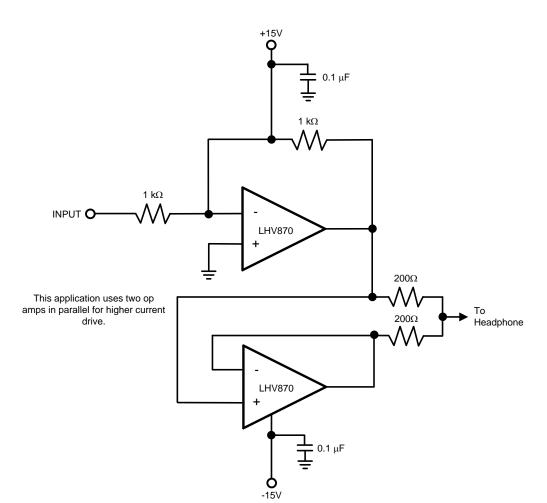


Figure 71. Headphone Amplifier



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REVISION HISTORY

Rev	Date	Description
1.0	05/25/11	Initial WEB released.
1.01	12/16/11	Changed the package from LCE10A to LCB10A.
1.02	01/04/12	Re-composed the document to reveal the LCB10A (revB) package.
2.0	05/02/13	layout of National Data Sheet to TI format

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Product Folder Links: LHV870



PACKAGE OPTION ADDENDUM

1-Oct-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins P	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LHV870LC/NOPB	OBSOLETE	UQFN	NKY	10		TBD	Call TI	Call TI		ZD1	
LHV870LCX/NOPB	OBSOLETE	UQFN	NKY	10		TBD	Call TI	Call TI		ZD1	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

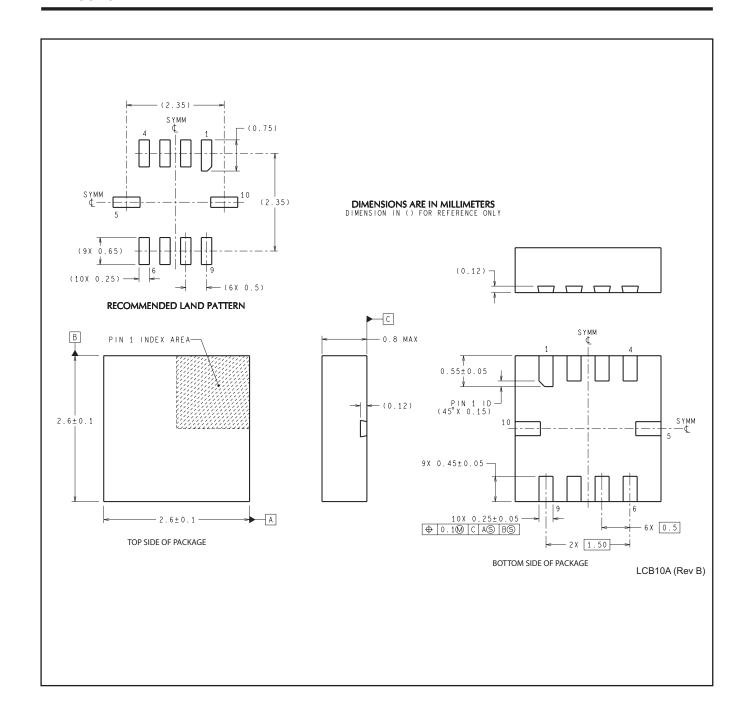
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